

# International IOR Rectifier

## UFB200FA40

### Ultrafast Soft Recovery Diode

#### Features

- Fast Recovery Time Characteristic
- Electrically Isolated Base Plate
- Large Creepage Distance Between Terminal
- Simplified Mechanical Designs, Rapid Assembly

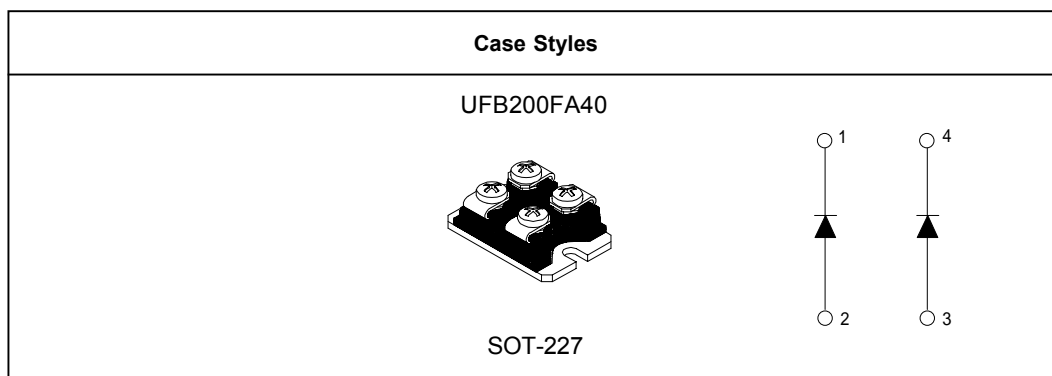
$V_R = 400V$
$V_F(\text{typ.}) = 1.0V$
$I_{F(AV)} = 200A$

#### Description

The dual diode series configuration (UFB200FA40) is used for output rectification or freewheeling/ clamping operation and high voltage application. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built. These modules are intended for general applications such as HV power supplies, HF welders, motor control and inverters.

#### Absolute Maximum Ratings

Parameters	Max	Units
$V_R$ Cathode-to-Anode Voltage	400	V
$I_F$ Continuous Forward Current, $T_C = 100^\circ C$ Per Leg	100	A
$I_{FSM}$ Single Pulse Forward Current, $T_C = 25^\circ C$ Per Leg	1300	
$I_{FRM}$ Maximum Repetitive Forward Current Per Leg	260	
Max. Power Dissipation, $T_C @ 90^\circ C$ Per Module	240	W
$V_{ISOL}$ RMS Isolation Voltage, Any Terminal to Case, $t = 1 \text{ min}$	2500	V
$T_J, T_{STG}$ Operating Junction and Storage Temperatures	- 55 to 150	$^\circ C$



**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified) per diode**

Parameters	Min	Typ	Max	Units	Test Conditions
V <sub>BR</sub> Cathode Anode Breakdown Voltage	400	-	-	V	I <sub>R</sub> = 100μA
V <sub>FM</sub> Forward Voltage	-	-	1.2	V	I <sub>F</sub> = 100A
	-	-	1.0	V	I <sub>F</sub> = 100A, T <sub>J</sub> = 150°C
I <sub>RM</sub> Reverse Leakage Current	-	-	50	μA	V <sub>R</sub> = V <sub>R</sub> Rated
	-	-	4	mA	T <sub>J</sub> = 150°C, V <sub>R</sub> = V <sub>R</sub> Rated
C <sub>T</sub> Junction Capacitance	-	100	-	pF	V <sub>R</sub> = 400V

**Dynamic Recovery Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified) per diode**

Parameters	Min	Typ	Max	Units	Test Conditions	
t <sub>rr</sub> Reverse Recovery Time	-	-	60	ns	I <sub>F</sub> = 1.0A, di <sub>F</sub> /dt = 200A/μs, V <sub>R</sub> = 30V  I <sub>F</sub> = 150A V <sub>R</sub> = 200V di <sub>F</sub> /dt = 200A/μs	
	-	93	-			T <sub>J</sub> = 25°C
	-	172	-			T <sub>J</sub> = 125°C
I <sub>RRM</sub> Peak Recovery Current	-	11	-	A	T <sub>J</sub> = 25°C	
	-	20	-		T <sub>J</sub> = 125°C	
Q <sub>rr</sub> Reverse Recovery Charge	-	490	-	nC	T <sub>J</sub> = 25°C	
	-	1740	-		T <sub>J</sub> = 125°C	

**Thermal - Mechanical Characteristics**

Parameters	Min	Typ	Max	Units
R <sub>thJC</sub> Junction to Case, Single Leg Conducting Both Leg Conducting			0.5	°C/W
			0.25	K/W
R <sub>thCS</sub> Case to Heat Sink, Flat, Greased Surface		0.05		
Wt Weight		30		g
T Mounting Torque		1.3		(N*m)

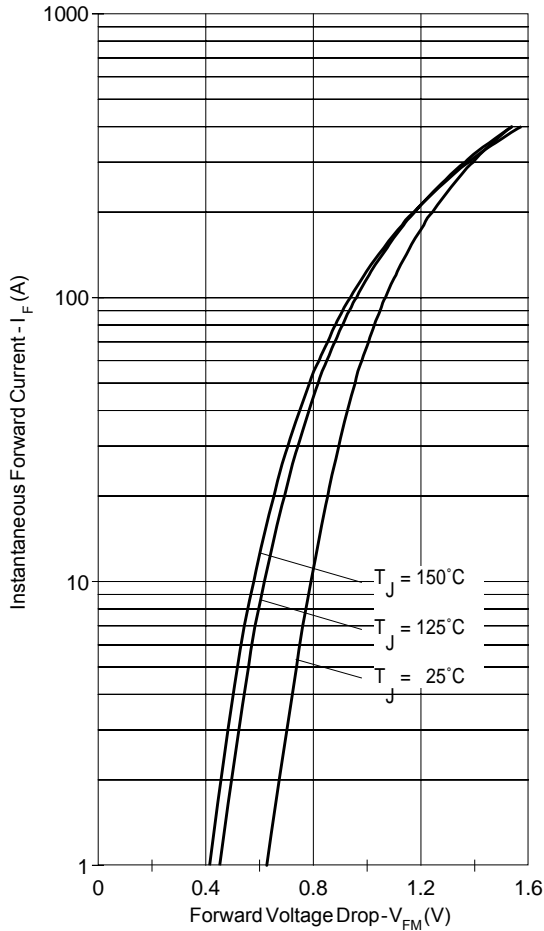


Fig. 1 - Typical Forward Voltage Drop Characteristics (per diode)

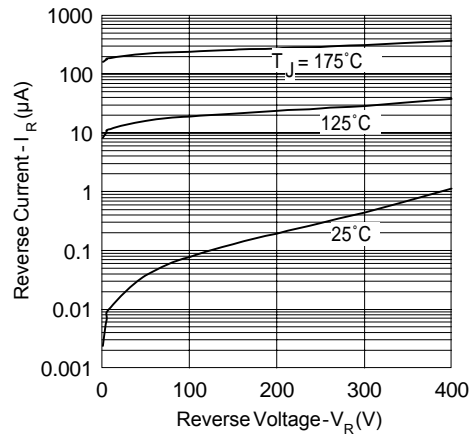


Fig. 2 - Typical Values Of Reverse Current Vs. Reverse Voltage

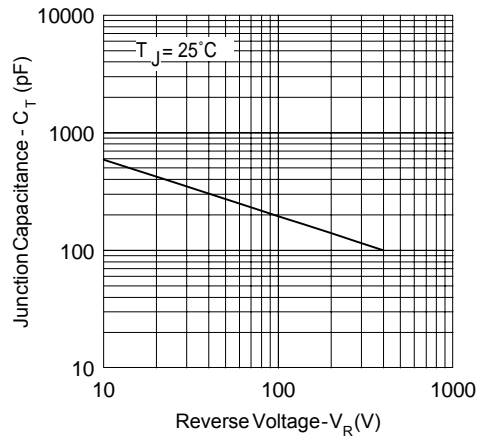


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

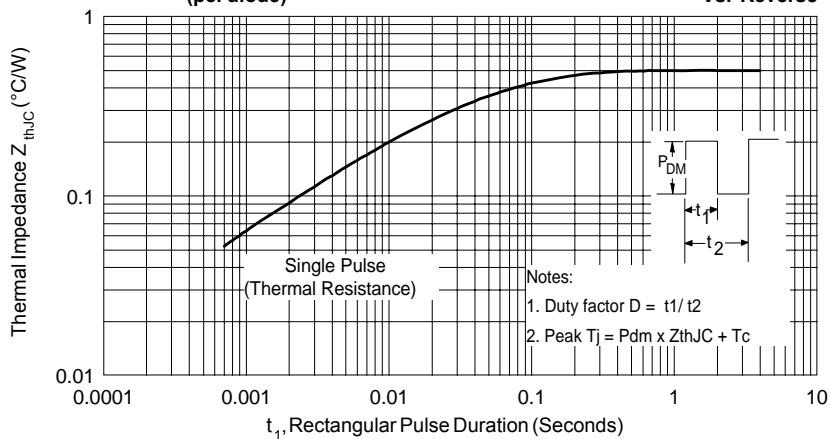


Fig. 4 - Max. Thermal Impedance  $Z_{thJC}$  Characteristics (per diode)

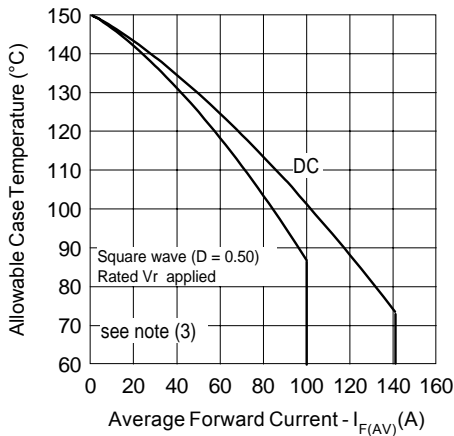


Fig. 5 - Max. Allowable Case Temperature Vs. Average Forward Current (per leg)

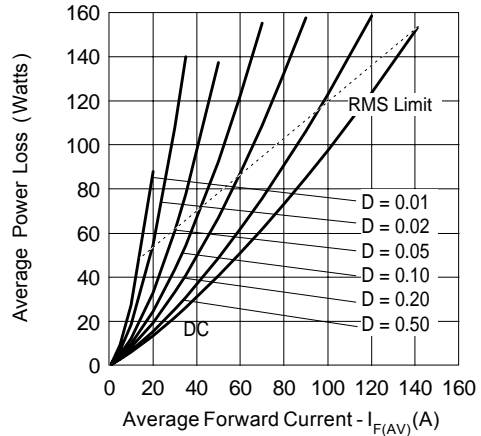


Fig. 6 - Forward Power Loss Characteristics (per leg)

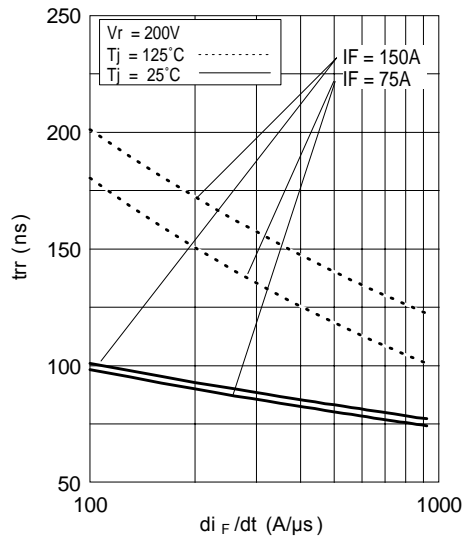


Fig. 7 - Typical Reverse Recovery time vs.  $di_F/dt$

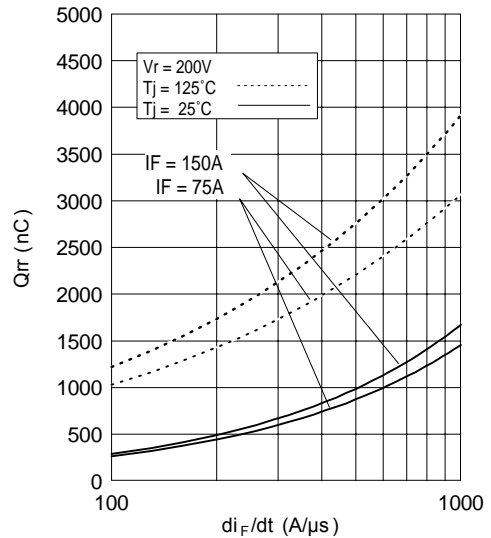


Fig. 8 - Typical Stored Charge vs.  $di_F/dt$

(3) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  
 $Pd$  = Forward Power Loss =  $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$  (see Fig. 6);  
 $Pd_{REV}$  = Inverse Power Loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R @ V_{R1} = 80\%$  rated  $V_R$

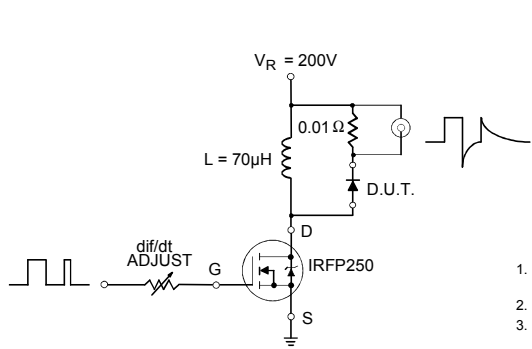
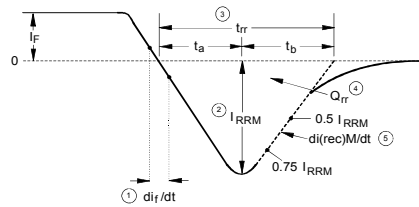


Fig. 1 - Reverse Recovery Parameter Test Circuit

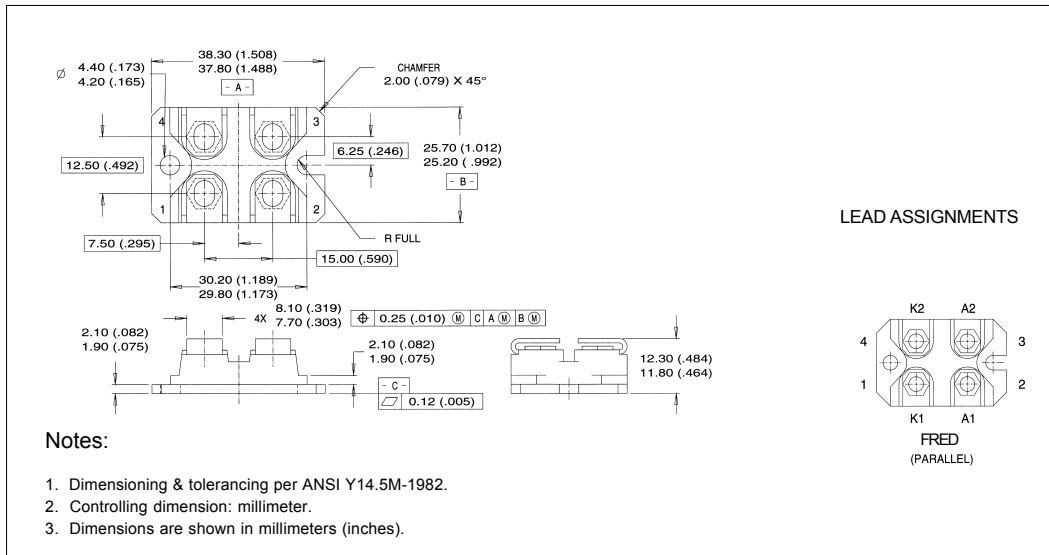


1.  $di_F/dt$  - Rate of change of current through zero crossing
2.  $I_{RRM}$  - Peak reverse recovery current
3.  $t_{rr}$  - Reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.5 I_{RRM}$  extrapolated to zero current
4.  $Q_{rr}$  - Area under curve defined by  $t_{rr}$  and  $I_{RRM}$   

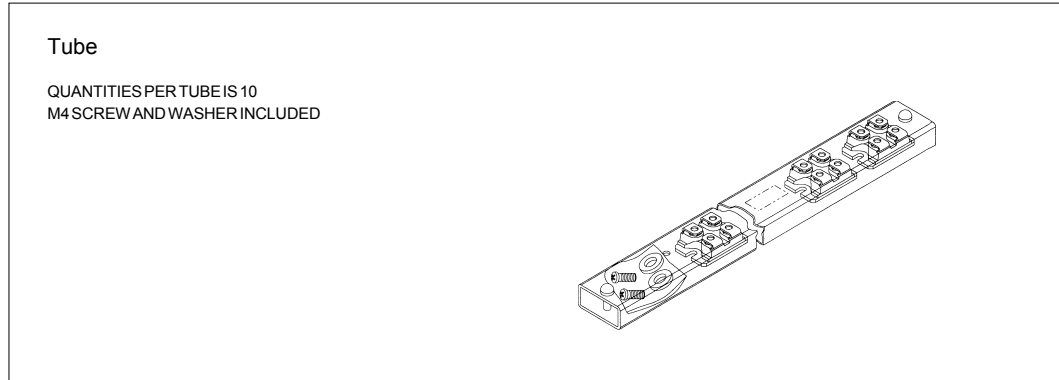
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$
5.  $di_{(rec)M}/dt$  - Peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 2 - Reverse Recovery Waveform and Definitions

SOT-227 Package Details



**SOT-227 Package Details**



**Ordering Information Table**

**Device Code**

UF	B	200	F	A	40	-
①	②	③	④	⑤	⑥	⑦

- 1** - ULTRAFast RECTIFIER
- 2** - Ultrafst Pt diffused
- 3** - Current Rating (200 = 200A)
- 4** - Circuit Configuration (2 separate Diodes, parallel pin-out)
- 5** - Package Indicator (SOT-227 Standard Isolated Base)
- 6** - Voltage Rating (40 = 400V)
- 7** - Special Options

Empty = No special Option  
LC = n.a.

Data and specifications subject to change without notice.  
This product has been designed and qualified for Industrial Level.  
Qualification Standards can be found on IR's Web site.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Vishay\(威世\)](#)